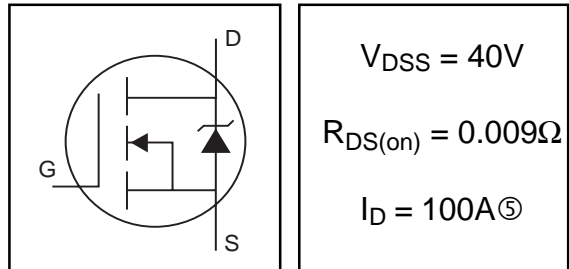


IRF1104S/L

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Surface Mount (IRF1104S)
- Low-profile through-hole (IRF1104L)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

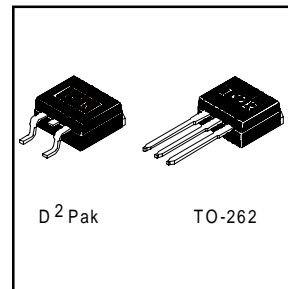


Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF1104L) is available for low-profile applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{\text{⑤}}$	100 ^⑥	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{\text{⑤}}$	71 ^⑥	
I_{DM}	Pulsed Drain Current ^{①⑤}	400	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	2.4	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	170	W
	Linear Derating Factor	1.1	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ^{②⑤}	350	mJ
I_{AR}	Avalanche Current ^①	60	A
E_{AR}	Repetitive Avalanche Energy ^①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ^{③⑤}	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

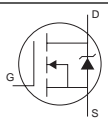
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.9	°C/W
$R_{\theta JA}$	Junction-to-Ambient(PCB Mounted, steady-state)**	—	62	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.038	—	V/°C	Reference to 25°C, I _D = 1mA ^⑤
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.009	Ω	V _{GS} = 10V, I _D = 60A ^④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	37	—	—	S	V _{DS} = 30V, I _D = 60A ^⑤
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 40V, V _{GS} = 0V
		—	—	250		V _{DS} = 32V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	93	nC	I _D = 60A
Q _{gs}	Gate-to-Source Charge	—	—	29		V _{DS} = 32V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	30		V _{GS} = 10V, See Fig. 6 and 13 ^{④⑤}
t _{d(on)}	Turn-On Delay Time	—	15	—	ns	V _{DD} = 20V
t _r	Rise Time	—	114	—		I _D = 60A
t _{d(off)}	Turn-Off Delay Time	—	28	—		R _G = 3.6Ω
t _f	Fall Time	—	19	—		R _D = 0.33Ω, See Fig. 10 ^{④⑤}
L _S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C _{iss}	Input Capacitance	—	2900	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1100	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	250	—		f = 1.0MHz, See Fig. 5 ^⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	100 ^⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ^①	—	—	400		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 60A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	74	110	ns	T _J = 25°C, I _F = 60A
Q _{rr}	Reverse Recovery Charge	—	188	280	nC	di/dt = 100A/μs ^{④⑤}
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
 - ② Starting T_J = 25°C, L = 194μH
R_G = 25Ω, I_{AS} = 60A. (See Figure 12)
 - ③ I_{SD} ≤ 60A, di/dt ≤ 304A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C
 - ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
 - ⑤ Uses IRF1104 data and test conditions.
 - ⑥ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4
- ** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

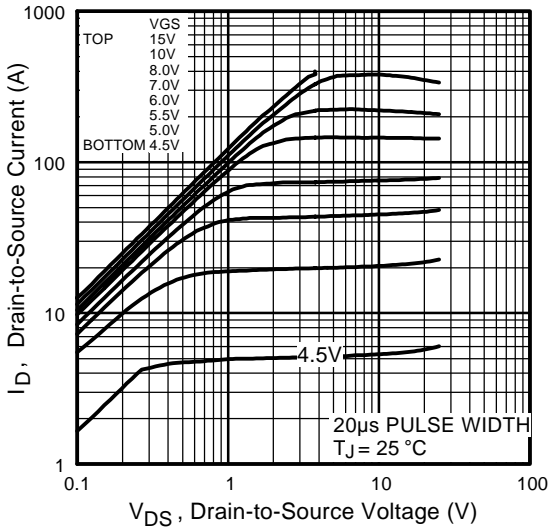


Fig 1. Typical Output Characteristics

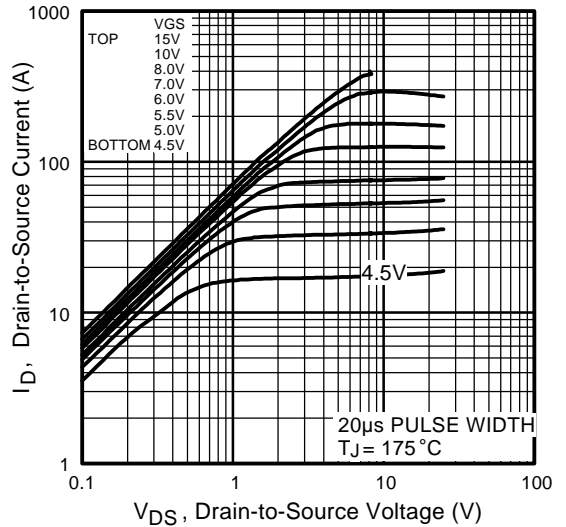


Fig 2. Typical Output Characteristics

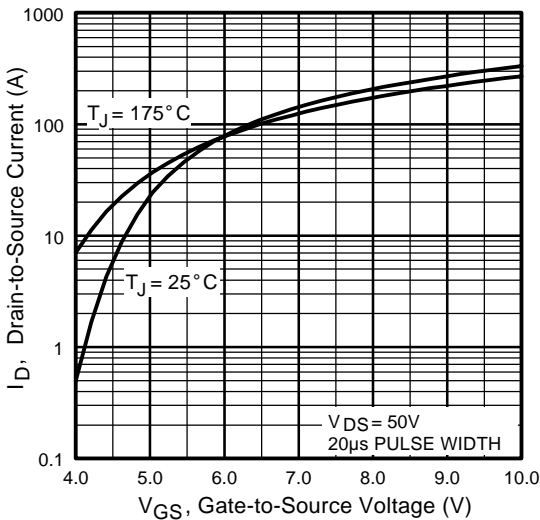


Fig 3. Typical Transfer Characteristics

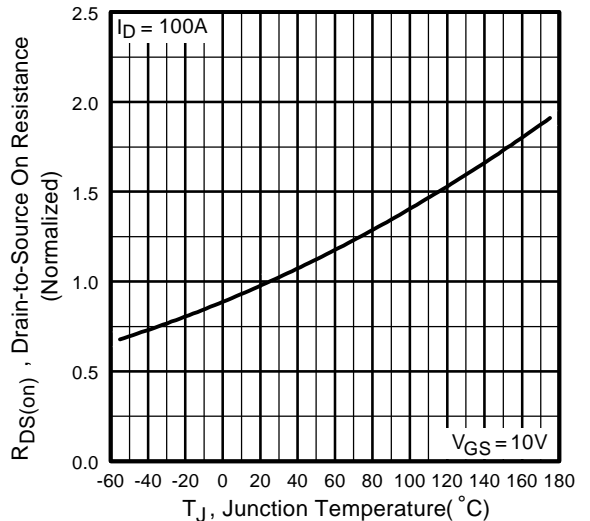


Fig 4. Normalized On-Resistance Vs. Temperature

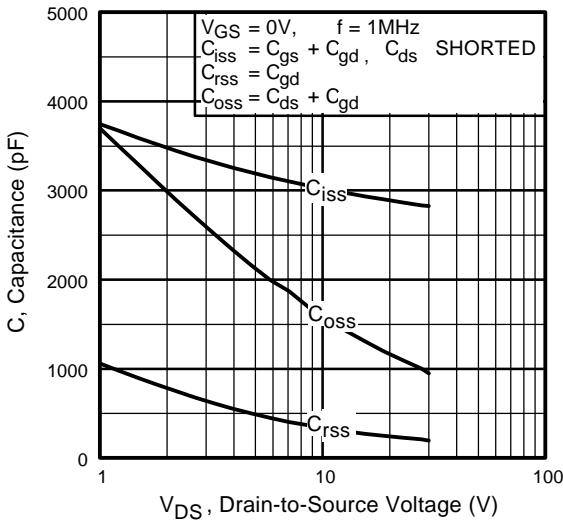


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

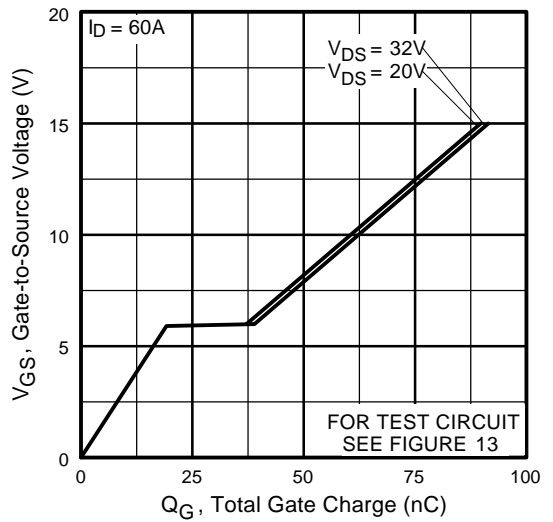


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

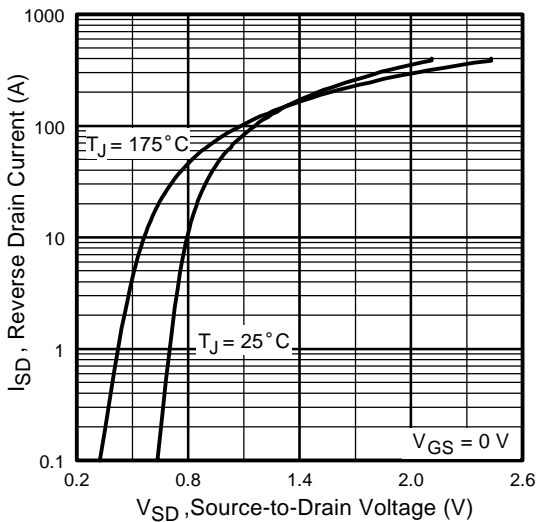


Fig 7. Typical Source-Drain Diode Forward Voltage

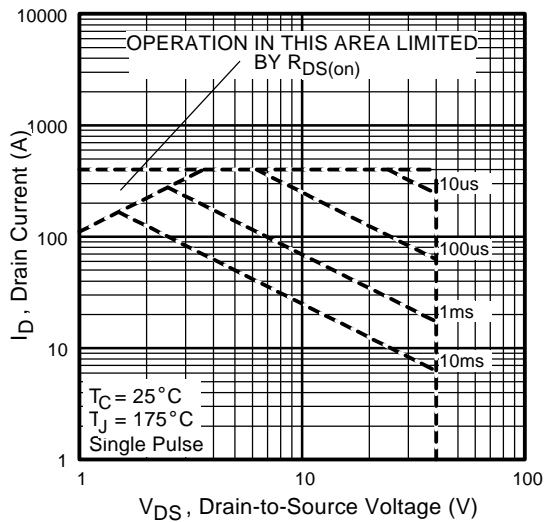


Fig 8. Maximum Safe Operating Area

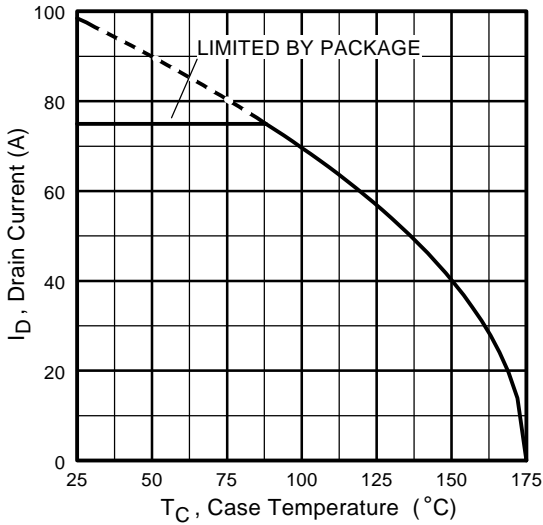


Fig 9. Maximum Drain Current Vs. Case Temperature

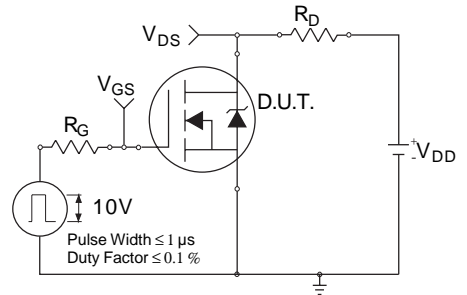


Fig 10a. Switching Time Test Circuit

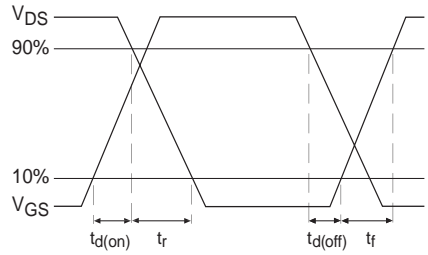


Fig 10b. Switching Time Waveforms

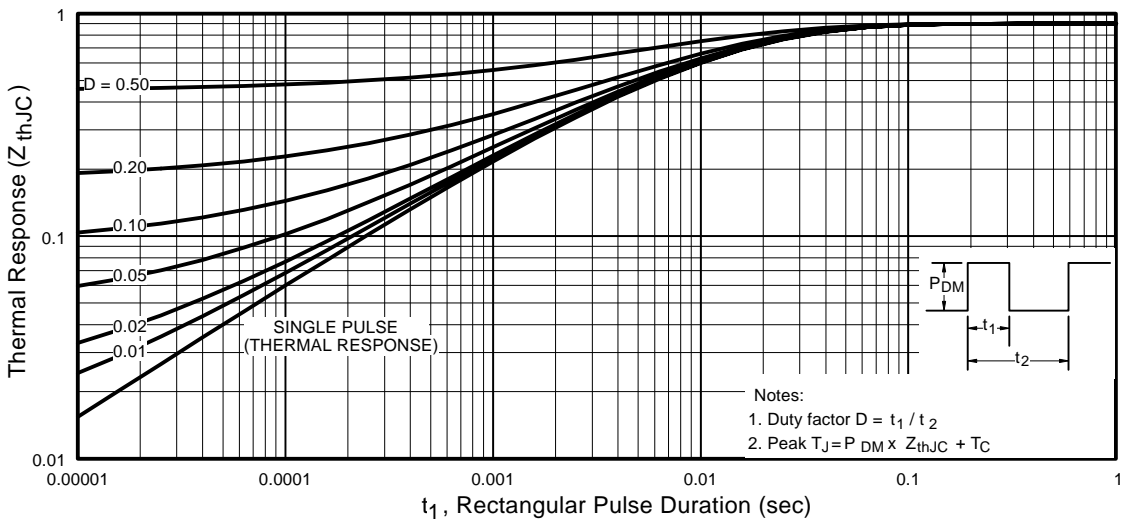


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

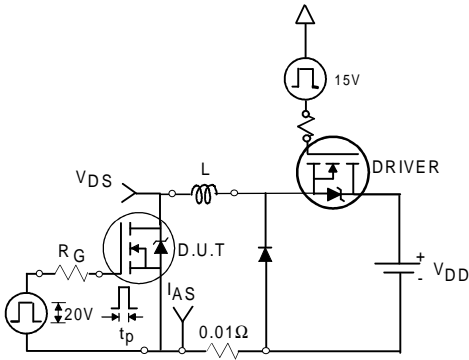


Fig 12a. Unclamped Inductive Test Circuit

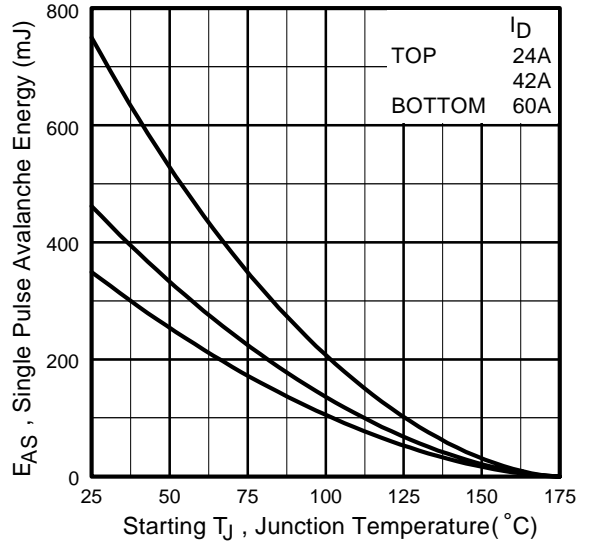


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

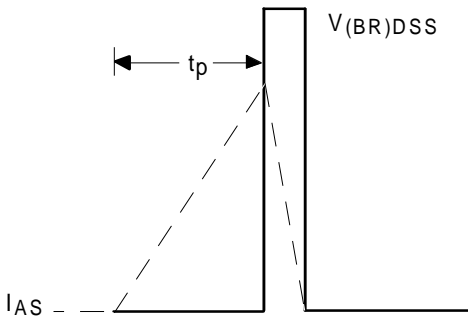


Fig 12b. Unclamped Inductive Waveforms

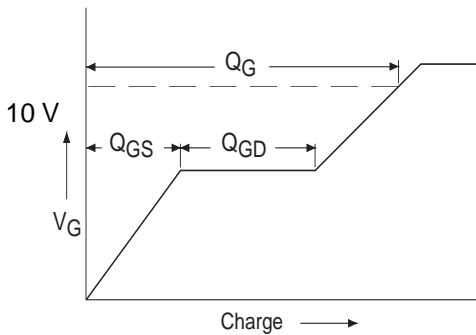


Fig 13a. Basic Gate Charge Waveform

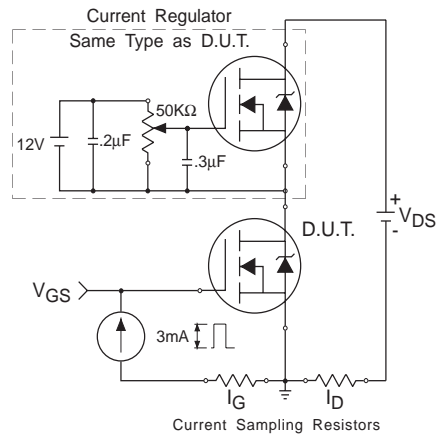
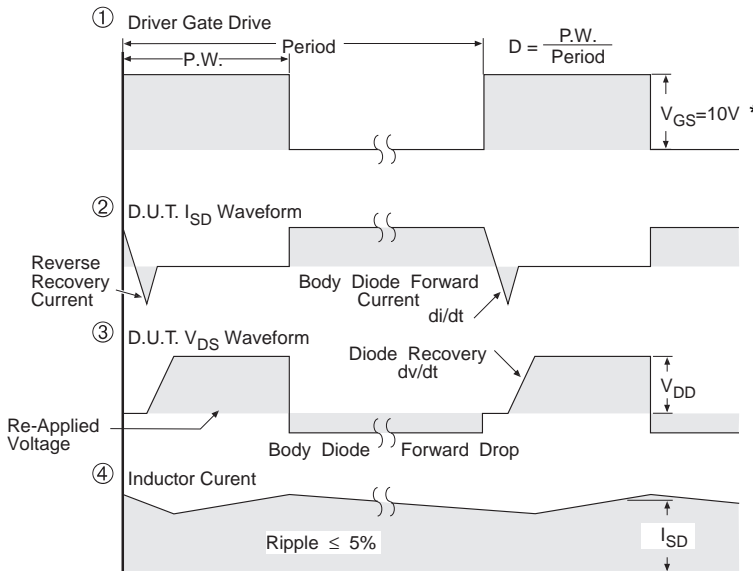
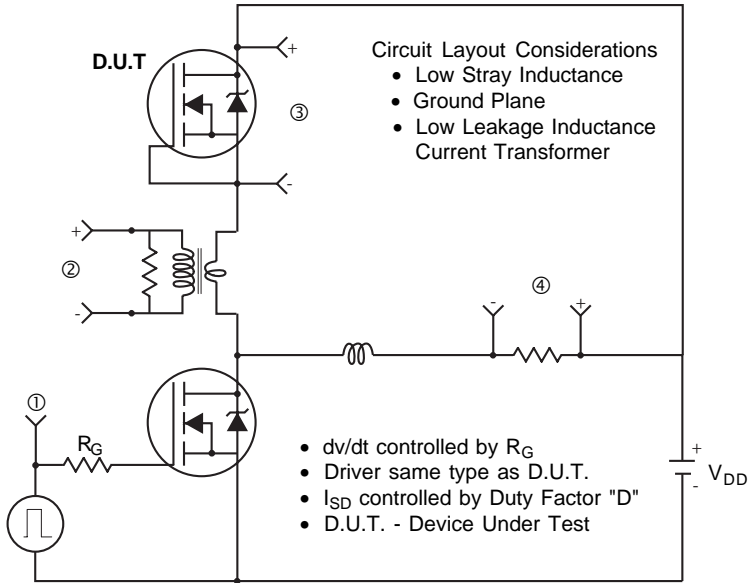


Fig 13b. Gate Charge Test Circuit

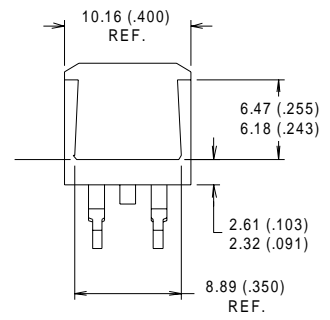
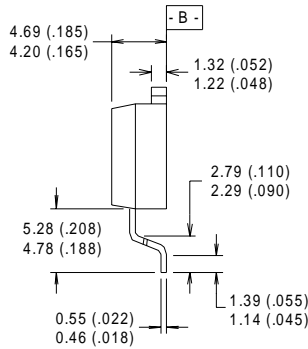
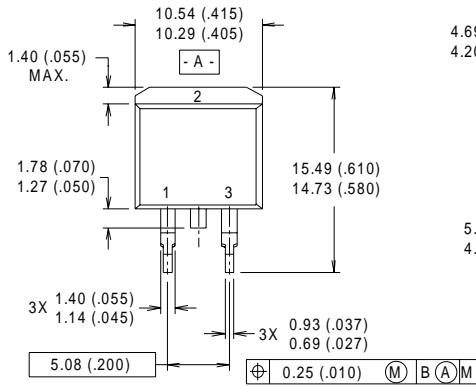
Peak Diode Recovery dv/dt Test Circuit



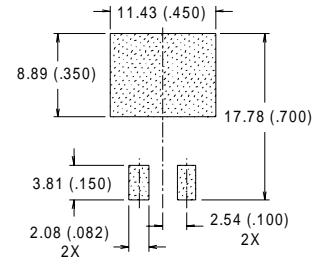
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

D²Pak Package Details



MINIMUM RECOMMENDED FOOTPRINT



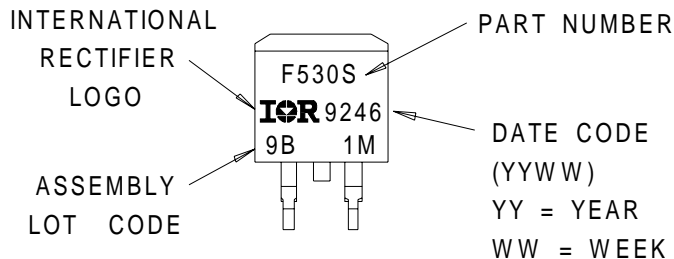
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

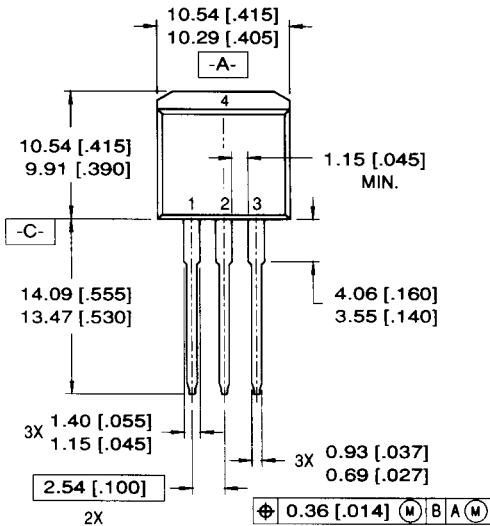
LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

Part Marking

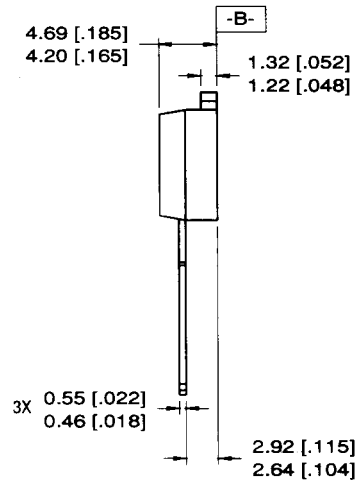


TO-262 Package Details



LEAD ASSIGNMENTS

- 1 = GATE 3 = SOURCE
2 = DRAIN 4 = DRAIN

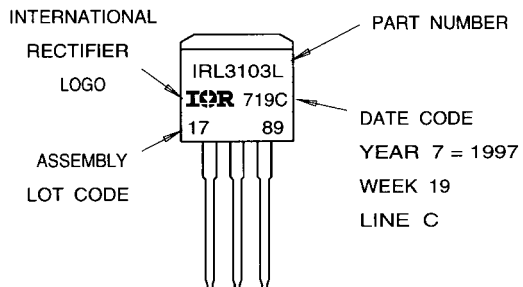


NOTES:

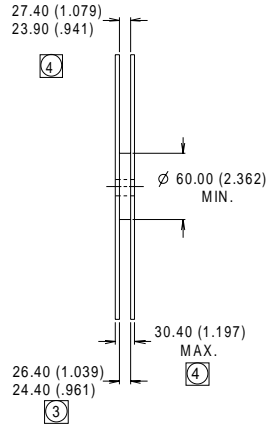
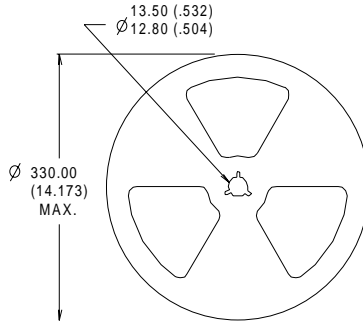
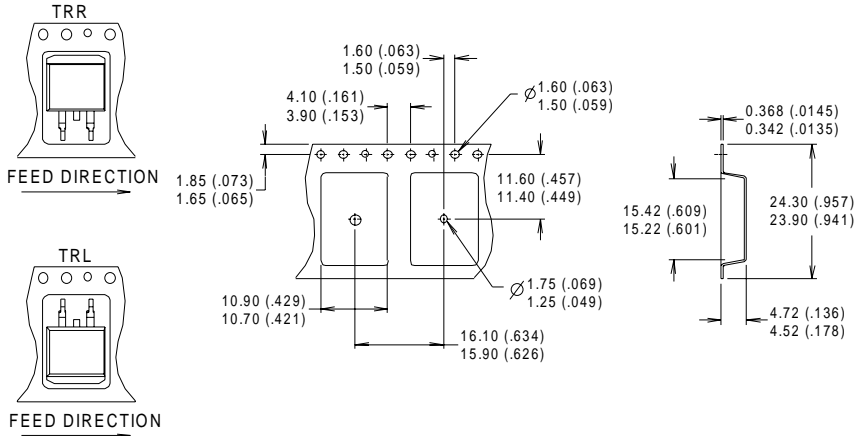
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

Part Marking

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



D²Pak Tape and Reel



- NOTES :
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 838 4630

IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>